PATENT ABSTRACTS OF JAPAN

(11)Publication number:

2000-232044

(43) Date of publication of application: 22.08.2000

(51)Int.Cl.

H01L 21/027

(21)Application number: 11-032028

(71)Applicant: NEC CORP

(22)Date of filing:

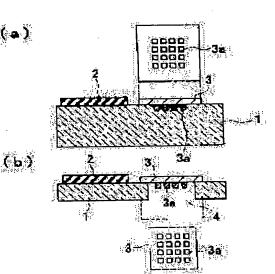
09.02.1999

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(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a manufacturing method of a semiconductor device, in which cracks and splits of a semiconductor substrate are hardly generated and alignment precision can be improved. SOLUTION: In this manufacturing method of a semiconductor device, a surface circuit pattern 2 is formed on the surface of the semiconductor device, and a pattern 3a for alignment is formed. After an alignment mark 3 for the back is formed by depositing metal or dielectrics on the pattern 3a for alignment and its peripheral region, a perpendicular through-trench 4 which reaches the alignment mark 3 for the back is formed in a region in the back of a semiconductor substrate, the region of which faces the alignment mark 3 in the back, and the alignment mark 3 for the back is exposed on the back surface side of the semiconductor substrate. The alignment mark 3 for the back is used as reference, and a



LEGAL STATUS

[Date of request for examination]

circuit pattern on the back is formed.

24.03.1999

[Date of sending the examiner's decision of

04.12.2001

rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]